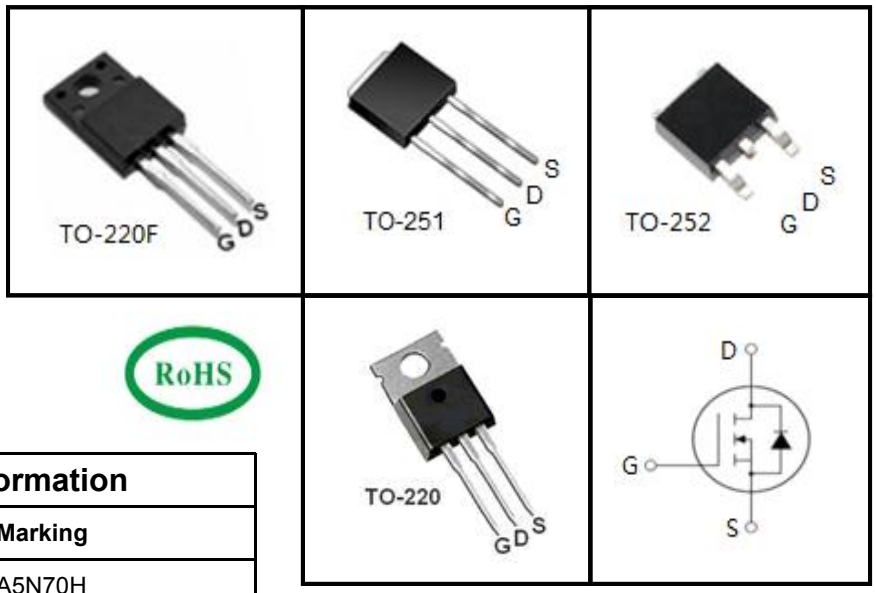
700V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



RoHS

Device Marking and Package Information		
Device	**Package**	**Marking**
TMA5N70H	TO-220F	A5N70H
TMP5N70H	TO-220	P5N70H
TMD5N70H	TO-252	D5N70H
TMU5N70H	TO-251	U5N70H

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter	Symbol	Value				Unit
		TO-220F	TO-220	TO-252	TO-251	
Drain-Source Voltage (V_{GS} = 0V)	V_{DSS}	700				V
Continuous Drain Current	I_D	5				A
Pulsed Drain Current (note1)	I_{DM}	20				A
Gate-Source Voltage	V_{GSS}	±30				V
Single Pulse Avalanche Energy (note2)	E_{AS}	176				mJ
Avalanche Current (note1)	I_{AR}	4.2				A
Repetitive Avalanche Energy (note1)	E_{AR}	35				mJ
Power Dissipation (T_C = 25ºC)	P_D	54	83			W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150				ºC

Thermal Resistance

Parameter	Symbol	Value				Unit
		TO-220F	TO-220	TO-252	TO-251	
Thermal Resistance, Junction-to-Case	R_{thJC}	2.3	1.5			ºC/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62.5	60			

Specifications T_J = 25ºC, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	700	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 700V, V_{GS} = 0V, T_J = 25ºC	--	--	1	μA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	3.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	V_{GS} = 10V, I_D = 2.5A	--	1.9	2.4	Ω
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1.0MHz	--	700	--	pF
Output Capacitance	C_{oss}		--	94	--	
Reverse Transfer Capacitance	C_{rss}		--	12	--	
Total Gate Charge	Q_g	V_{DD} = 560V, I_D = 5A, V_{GS} = 10V	--	19	--	nC
Gate-Source Charge	Q_{gs}		--	3.7	--	
Gate-Drain Charge	Q_{gd}		--	11	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 350V, I_D = 5A, R_G = 25 Ω	--	13	--	ns
Turn-on Rise Time	t_r		--	20	--	
Turn-off Delay Time	$t_{d(off)}$		--	76	--	
Turn-off Fall Time	t_f		--	40	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25 ºC	--	--	5	A
Pulsed Diode Forward Current	I_{SM}		--	--	20	
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 6A, V_{GS} = 0V	--	--	1.4	V
Reverse Recovery Time	t_{rr}	V_{GS} = 0V,I_S = 6A, di_F/dt =100A /μs	--	260	--	ns
Reverse Recovery Charge	Q_{rr}		--	3.8	--	μC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. I_{AS} = 4.2A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25 ºC
3. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 1%

Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics (T_J = 25ºC)

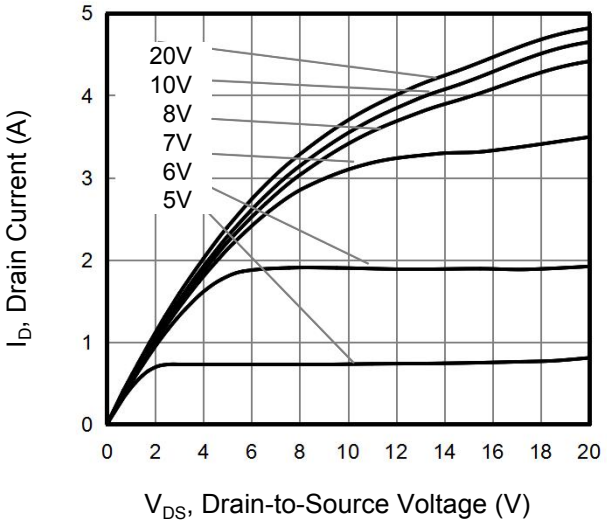


Figure 2. Body Diode Forward Voltage

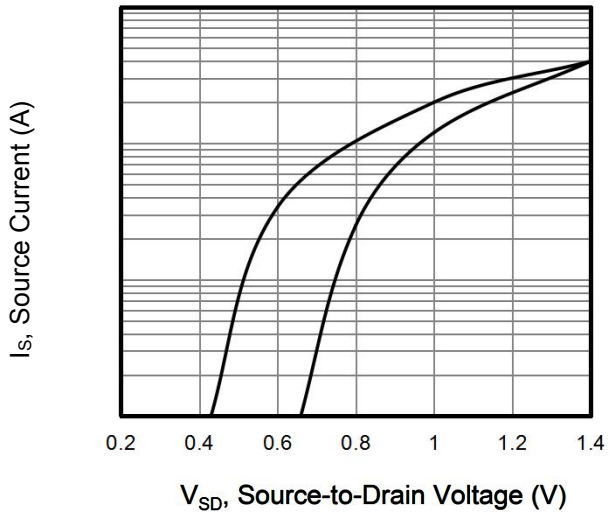


Figure 3. Drain Current vs. Temperature

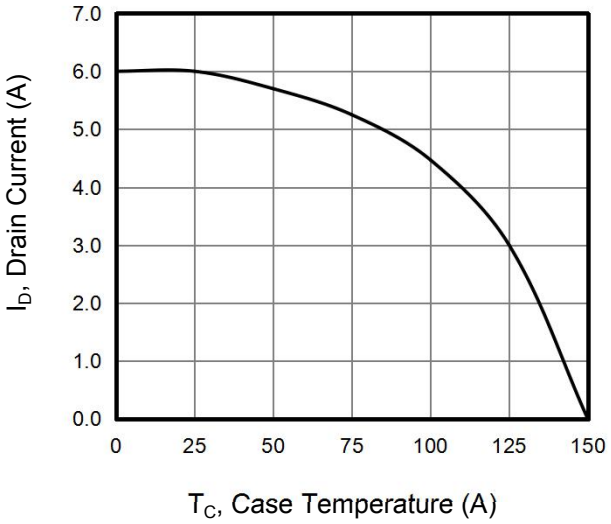


Figure 4. BV_{DSS} Variation vs. Temperature

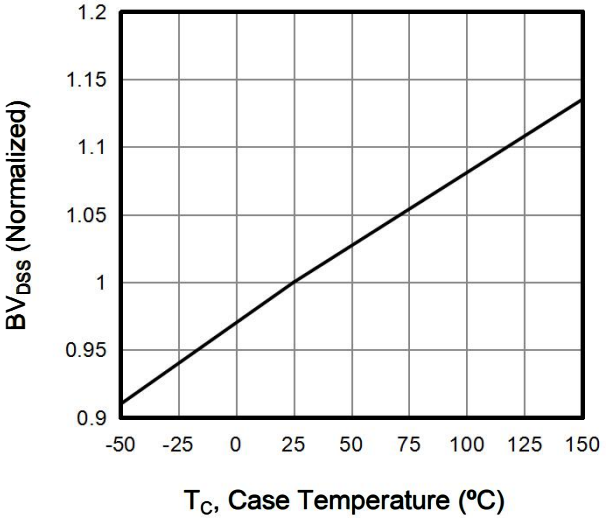


Figure 5. Transfer Characteristics

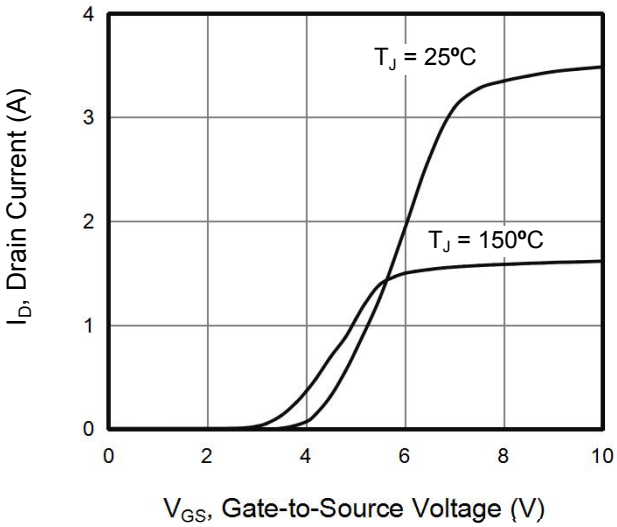
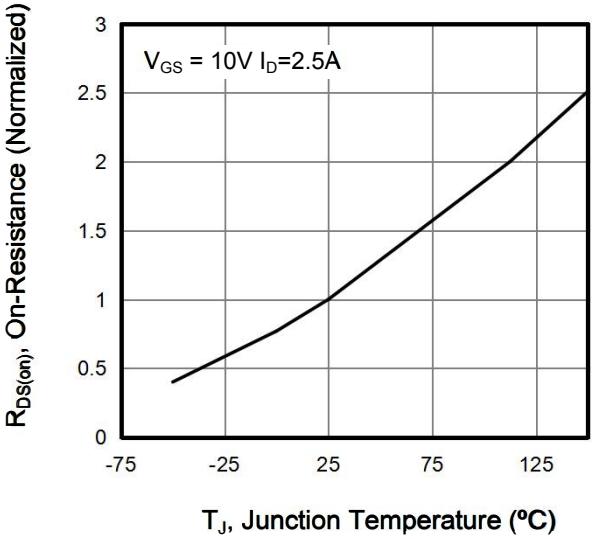


Figure 6. On-Resistance vs. Temperature



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Capacitance

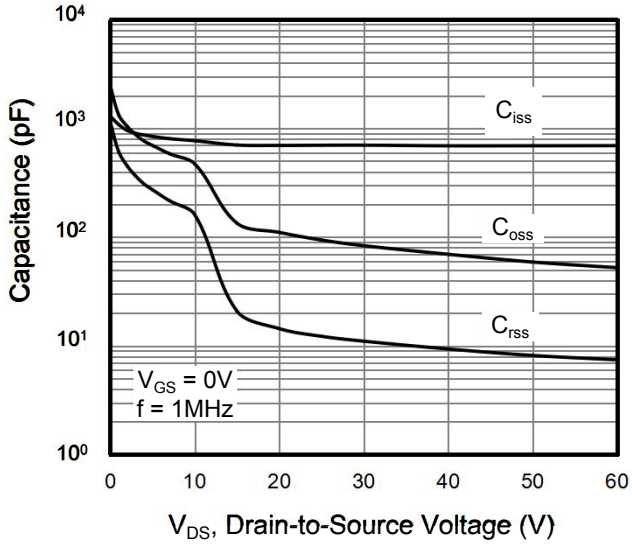


Figure 8. Gate Charge

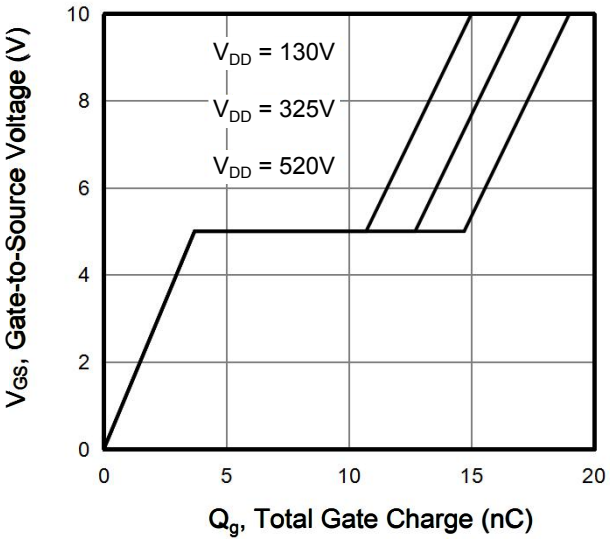


Figure 9. Transient Thermal Impedance

TO-220,TO-251,TO-252

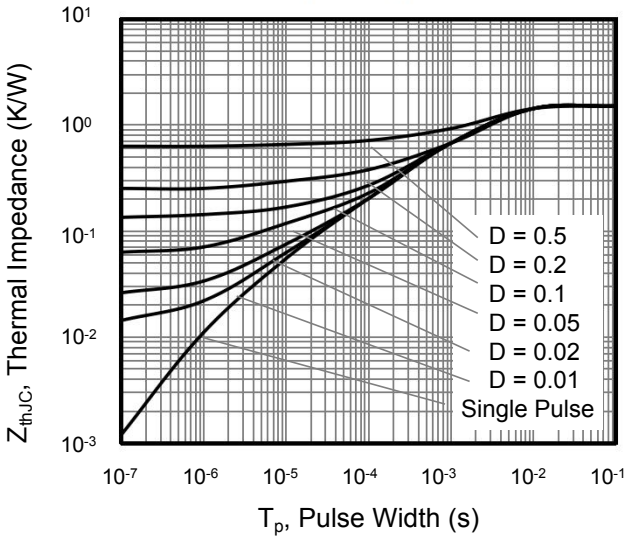


Figure 10. Transient Thermal Impedance

TO-220F

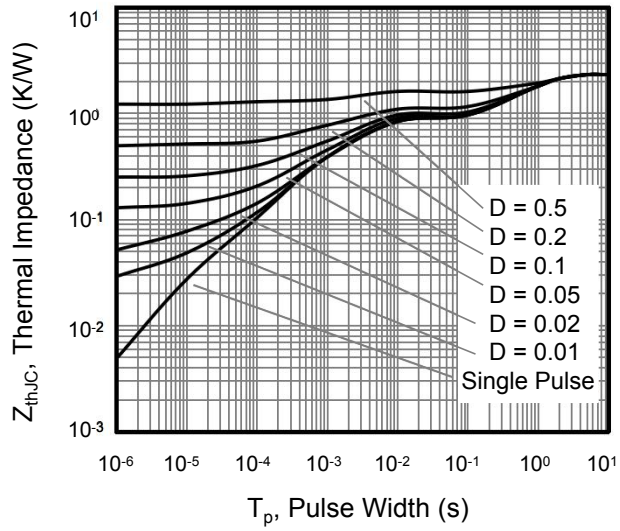


Figure A：Gate Charge Test Circuit and Waveform

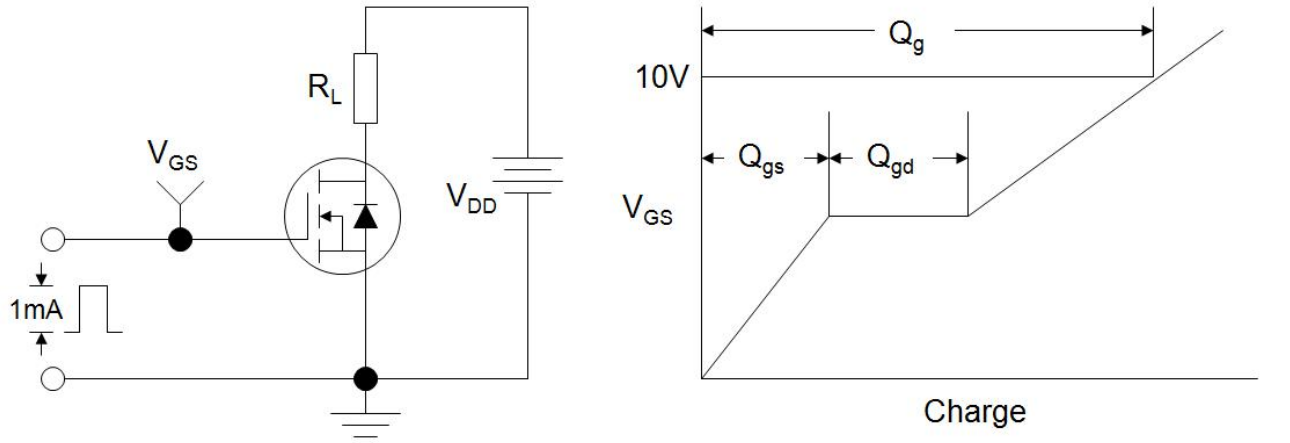


Figure B：Resistive Switching Test Circuit and Waveform

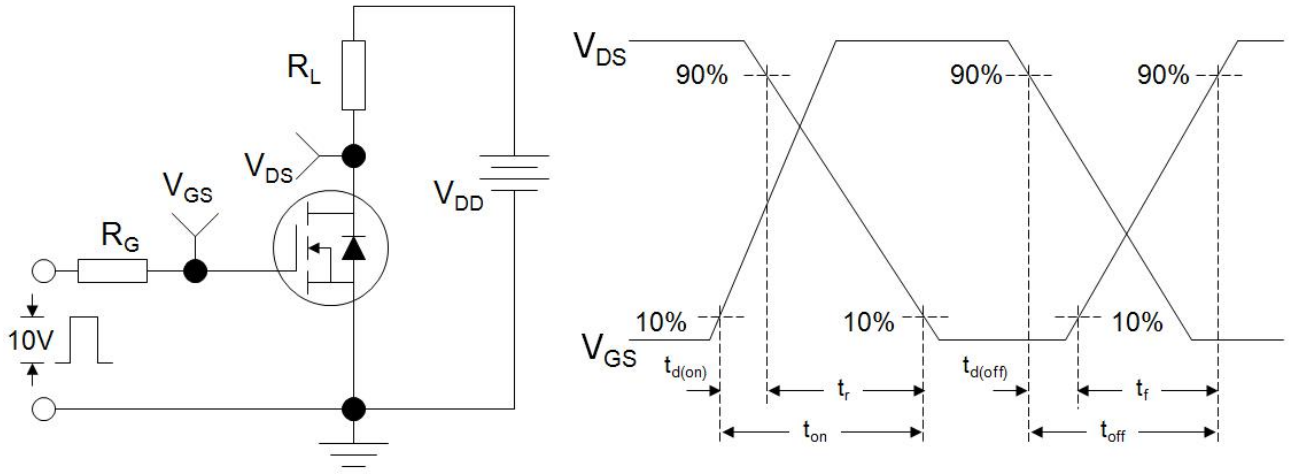
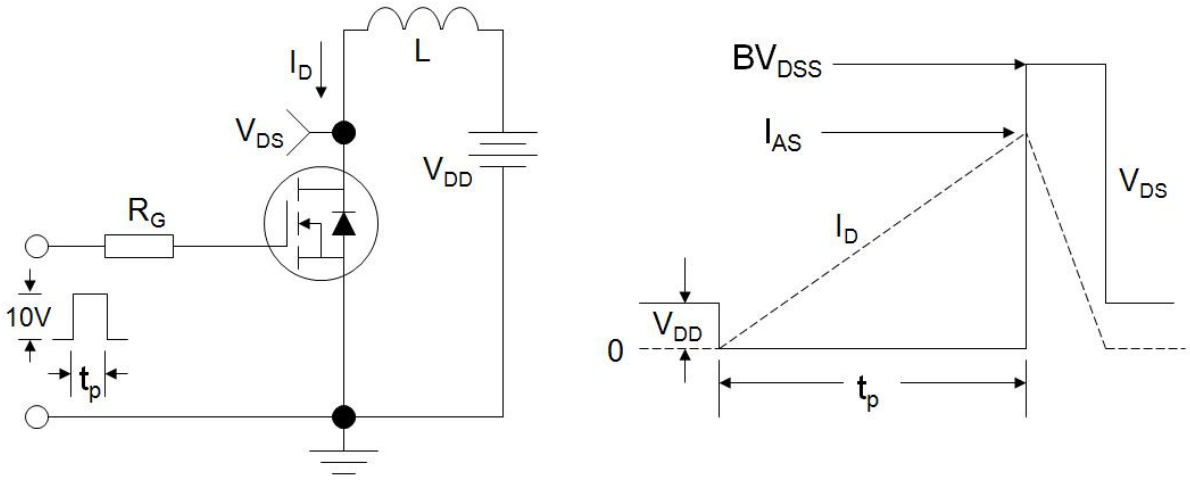
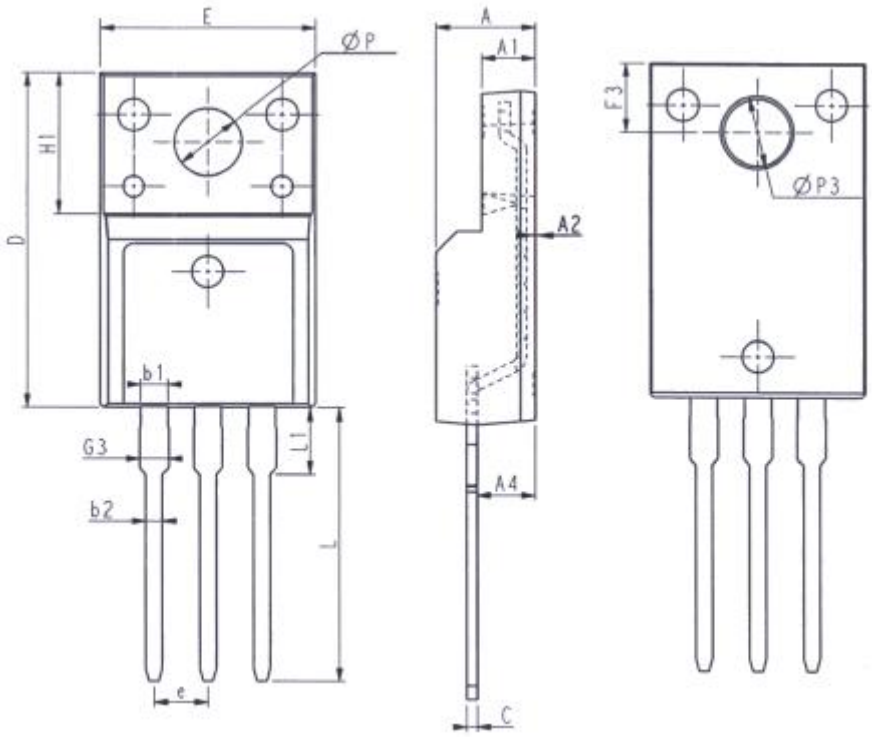


Figure C：Unclamped Inductive Switching Test Circuit and Waveform



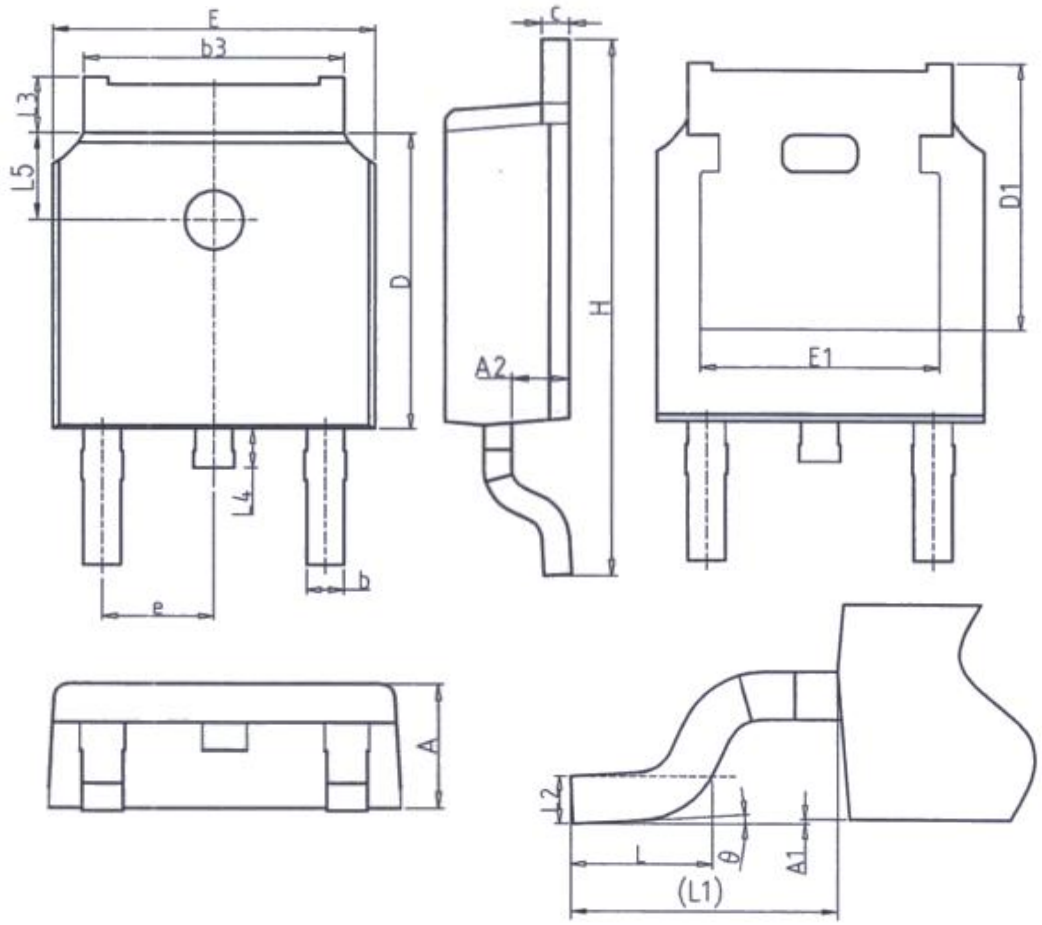
TO-220F



Unit: mm		
Symbol	Min.	Max.
E	9.96	10.36
A	4.50	4.90
A1	2.34	2.74
A2	0.30	0.60
A4	2.56	2.96
c	0.40	0.65
D	15.57	16.17
H1	6.70REF	
e	2.54BSC	

Unit: mm		
Symbol	Min.	Max.
L	12.68	13.28
L1	2.93	3.13
P	3.03	3.38
P3	3.15	3.65
F3	3.15	3.45
G3	1.25	1.55
b1	1.18	1.43
b2	0.70	0.95

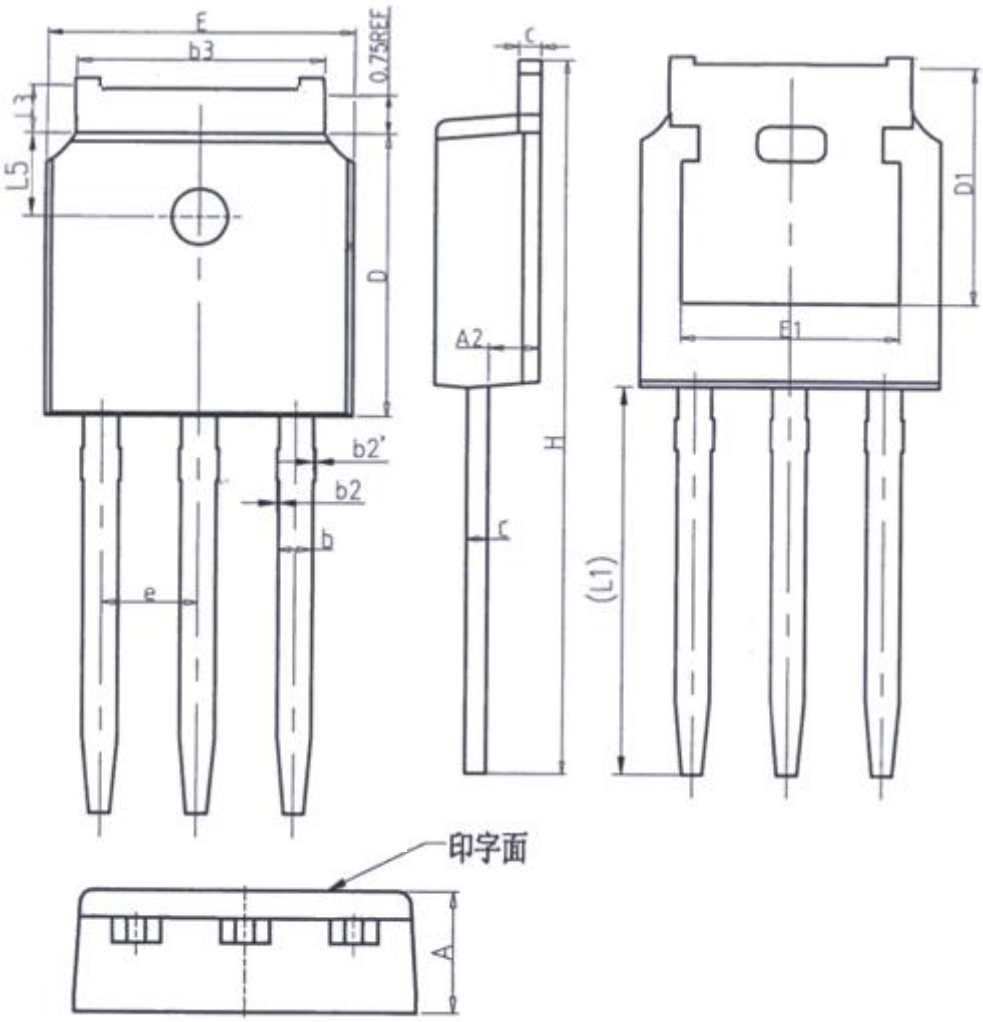
TO-252



Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A1	0.00	0.20
A2	0.97	1.17
b	0.68	0.90
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22
D1	5.30REF	
E	6.40	6.80
E1	4.63	–

Unit: mm		
Symbol	Min.	Max.
e	2.286BSC	
H	9.40	10.50
L	1.38	1.75
L1	2.90REF	
L2	0.51BSC	
L3	0.88	1.28
L4	–	1.00
L5	1.65	1.95
θ	0°	8°

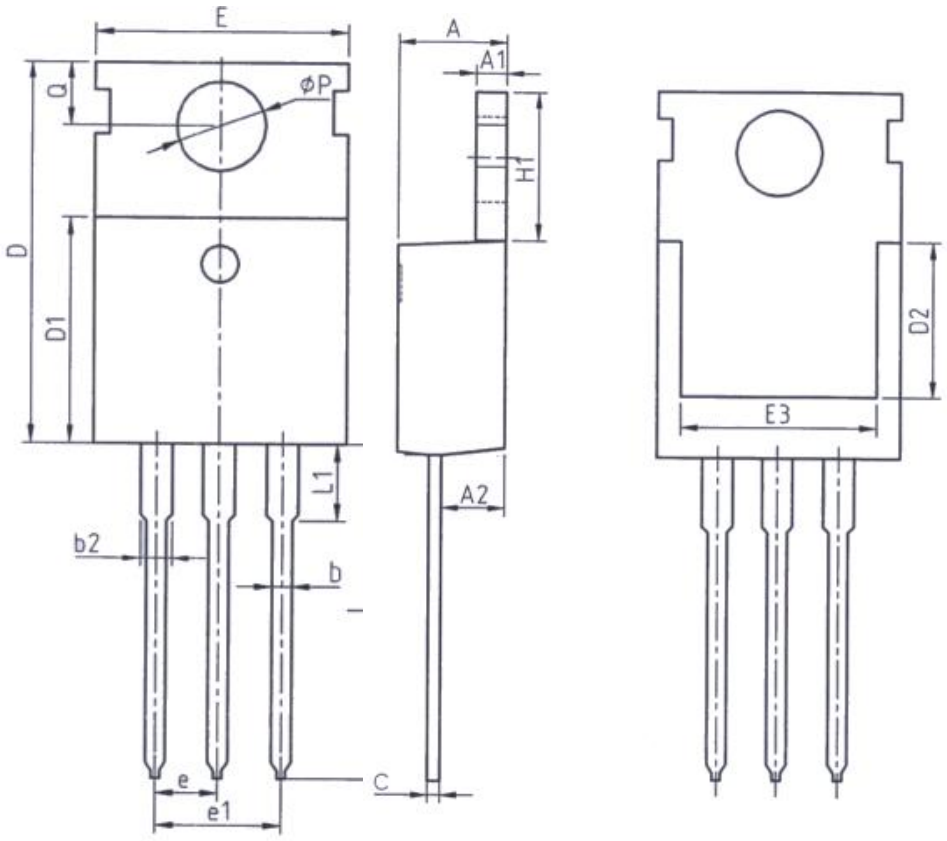
TO-251



Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A2	0.97	1.17
b	0.68	0.90
b2	0.00	0.10
b2′	0.00	0.10
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22

Unit: mm		
Symbol	Min.	Max.
D1	5.30REF	
E	6.40	6.80
E1	4.63	-
e	2.286BSC	
H	16.22	16.82
L1	9.15	9.65
L3	0.88	1.28
L5	1.65	1.95

TO-220



Unit: mm		
Symbol	Min.	Max.
A	4.37	4.77
A1	1.25	1.45
A2	2.20	2.60
b	0.70	0.95
b2	1.17	1.47
c	0.40	0.65
D	15.10	16.10
D1	8.80	9.40
D2	5.50	–

Unit: mm		
Symbol	Min.	Max.
E	9.70	10.30
E3	7.00	–
e	2.54BSC	
e1	5.08BSC	
H1	6.25	6.85
L	12.75	13.80
L1	–	3.40
P	3.40	3.80
Q	2.60	3.00

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